

Features

- Uses CRM(CQ) advanced SkyMOS4 technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g \times R_{DS(on)}$ product(FOM)
- Qualified according to JEDEC criteria

Product Summary

V_{DS}	100V
$R_{DS(on).typ}$	1.2mΩ
I_D	370A

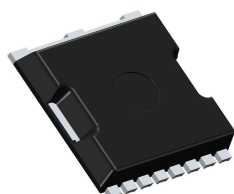
Applications

- DCDC Converter
- Switching applications

100% DVDS Tested
100% Avalanche Tested

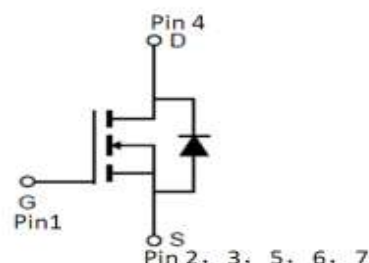
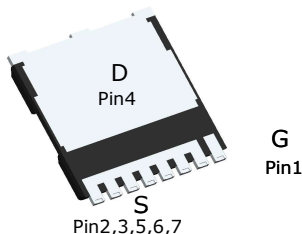


Top View



CRSZ015N10N4Z

Bottom View



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRSZ015N10N4Z	015N10N4Z	TOLL	Tape&Reel	N/A	N/A	2000pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	100	V
Continuous drain current	I_D	410	A
$T_C = 25^\circ\text{C}$ (Silicon limit)		370	
$T_C = 25^\circ\text{C}$ (Package limit)		260	
$T_C = 100^\circ\text{C}$ (Silicon limit)			
Pulsed drain current ($T_C = 25^\circ\text{C}$, t_p limited by T_{jmax})	$I_{D \text{ pulse}}$	1480	A
Avalanche energy, single pulse ($I_D = 88\text{A}$, $R_g = 25\Omega$) ^[1]	E_{AS}	1936	mJ
Gate-Source voltage	V_{GS}	± 20	V
Power dissipation ($T_C = 25^\circ\text{C}$)	P_{tot}	437	W
Operating junction and storage temperature	T_j, T_{stg}	-55...+150	°C
Soldering temperature, wave soldering only allowed at leads (1.6mm from case for 10s)	T_{sold}	260	°C

※. Notes:

EAS is tested at starting $T_j = 25^\circ\text{C}$, $L = 0.5\text{mH}$, $I_{AS} = 88\text{A}$, $V_{GS} = 10\text{V}$.

Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – case.	R_{thJC}	0.29	°C/W
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}	42	

Electrical Characteristic (at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV_{DSS}	100	-	-	V	$V_{GS}=0V, I_D=250\mu A$
		100	-	-	V	$V_{GS}=0V, I_D=1mA$
Gate threshold voltage	$V_{GS(th)}$	2.0	3.0	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=100V, V_{GS}=0V$ $T_j=25^{\circ}\text{C}$
		-	-	100		$T_j=125^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}	-	-	± 100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	1.2	1.5	mΩ	$V_{GS}=10V, I_D=100A$
Transconductance	g_{fs}	128	255	510	S	$V_{DS}=5V, I_D=100A$

Dynamic Characteristic

Input Capacitance	C_{iss}	9261	13891	20837	pF	$V_{GS}=0V, V_{DS}=50V,$ $f=1MHz$
Output Capacitance	C_{oss}	1463	2195	3293		
Reverse Transfer Capacitance	C_{rss}	13	40	120		
Gate Total Charge	Q_G	129	193	290	nC	$V_{GS}=10V, V_{DS}=50V,$ $I_D=100A, f=1MHz$
Gate-Source charge	Q_{gs}	56	84	126		
Gate-Drain charge	Q_{gd}	13	26	52		
Turn-on delay time	$t_{d(on)}$	22	44	88	ns	$V_{GS}=10V, V_{DD}=50V,$ $R_{G_ext}=3\Omega$
Rise time	t_r	52	78	117		
Turn-off delay time	$t_{d(off)}$	63	95	143		
Fall time	t_f	31	46	69		
Gate resistance	R_G	-	1.5	4.5	Ω	$V_{GS}=0V, V_{DS}=0V,$ $f=1MHz$

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Diode continuous forward current	I_S	-	-	370	A	$T_C = 25^{\circ}\text{C}$
Diode pulse current	I_S pulse	-	-	1480	A	$T_C = 25^{\circ}\text{C}$
Body Diode Forward Voltage	V_{SD}	-	0.84	1.4	V	$V_{GS}=0V, I_{SD}=100A$
Body Diode Reverse Recovery Time	t_{rr}	53	105	210	ns	$I_F=100A, dI/dt=100A/\mu s$
Body Diode Reverse Recovery Charge	Q_{rr}	160	320	640	nC	

Typical Performance Characteristics

Fig 1: Output Characteristics

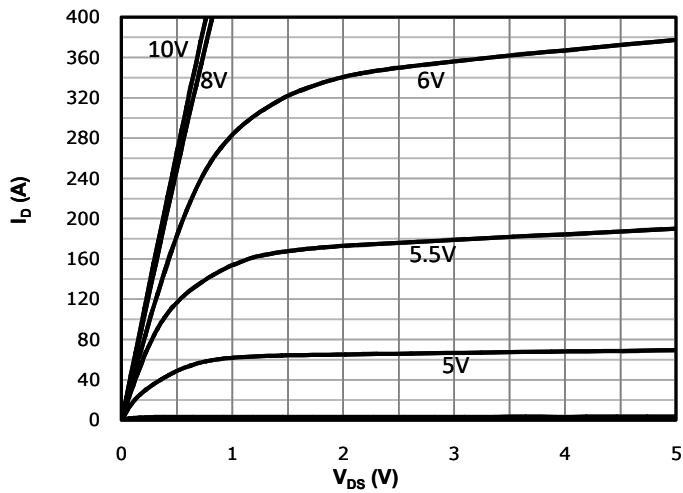


Fig 2: Transfer Characteristics

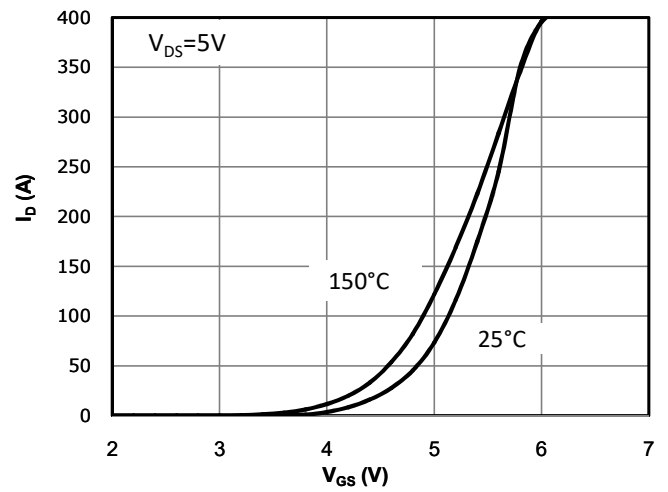


Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

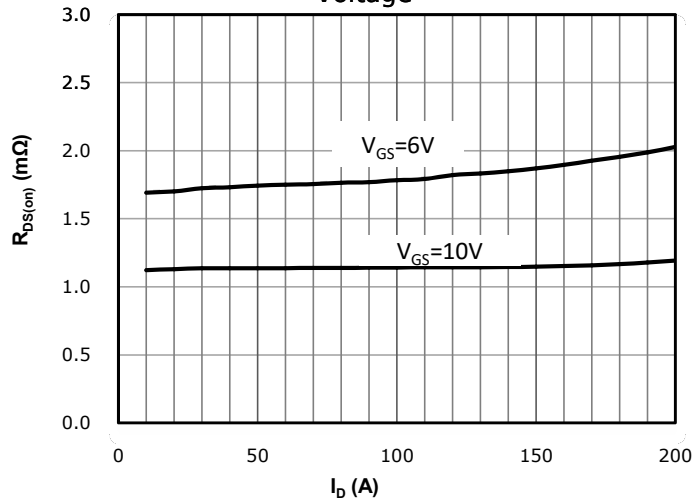


Fig 4: $R_{DS(on)}$ vs Gate Voltage

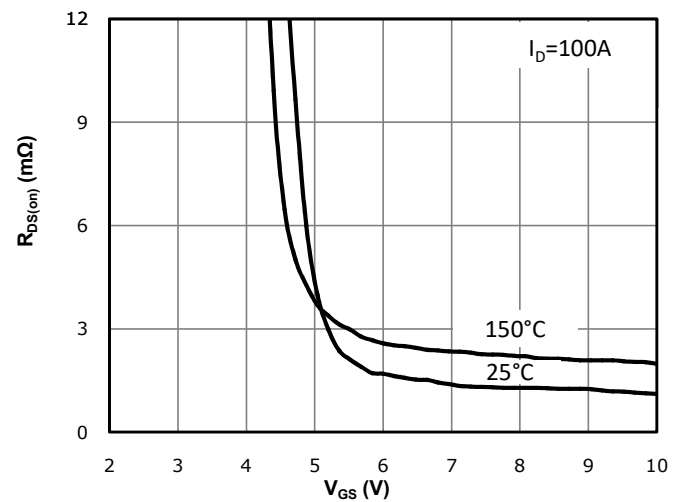


Fig 5: $R_{DS(on)}$ vs. Temperature

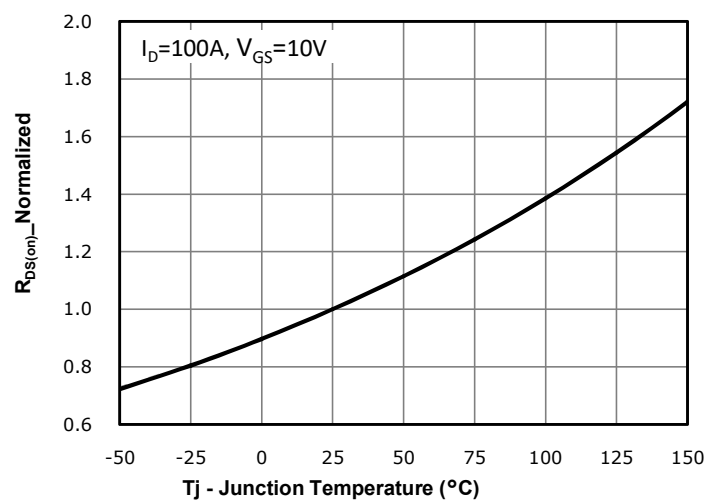


Fig 6: $V_{GS(th)}$ vs. Temperature

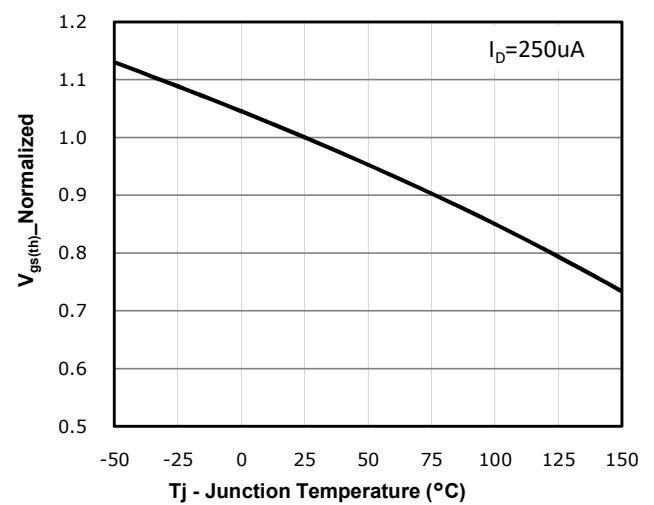


Fig 7: BVDss vs. Temperature

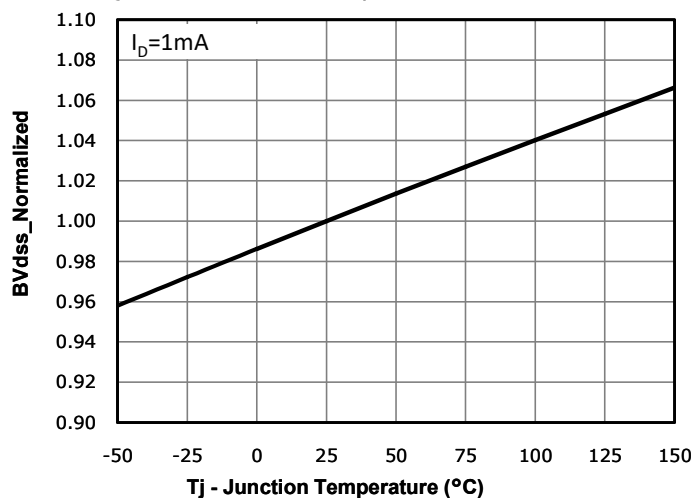


Fig 8: Capacitance Characteristics

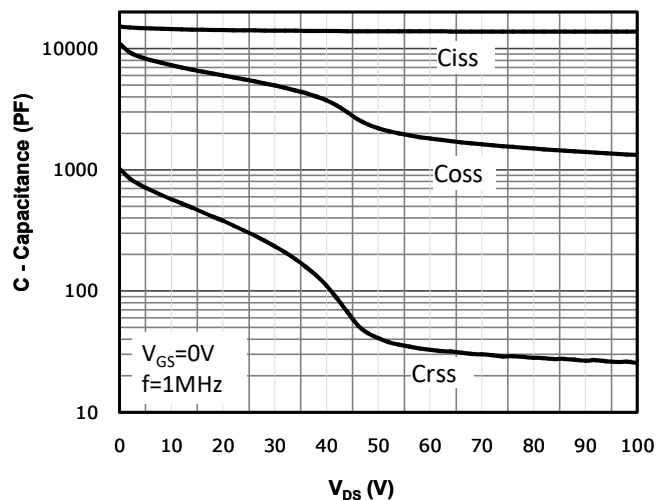


Fig 9: Gate Charge Characteristics

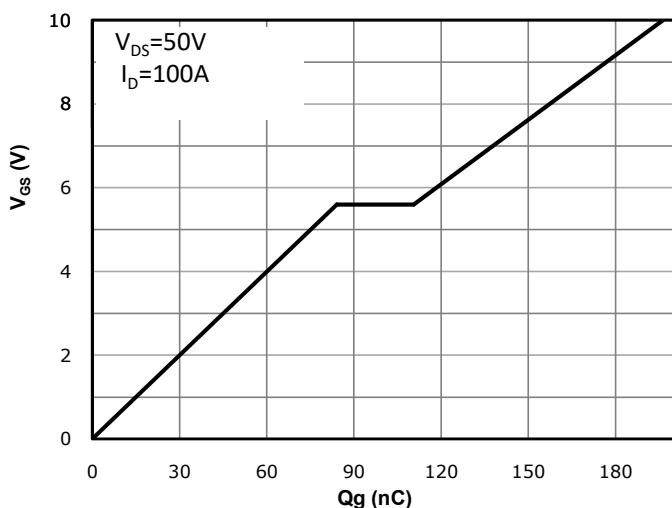


Fig 10: Body-diode Forward Characteristics

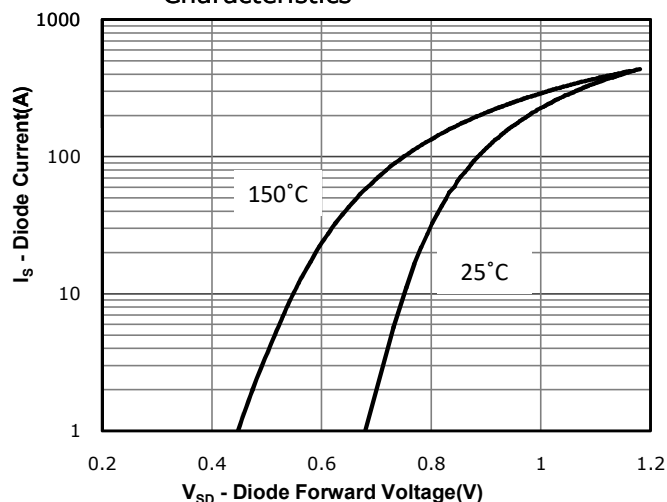


Fig 11: Power Dissipation

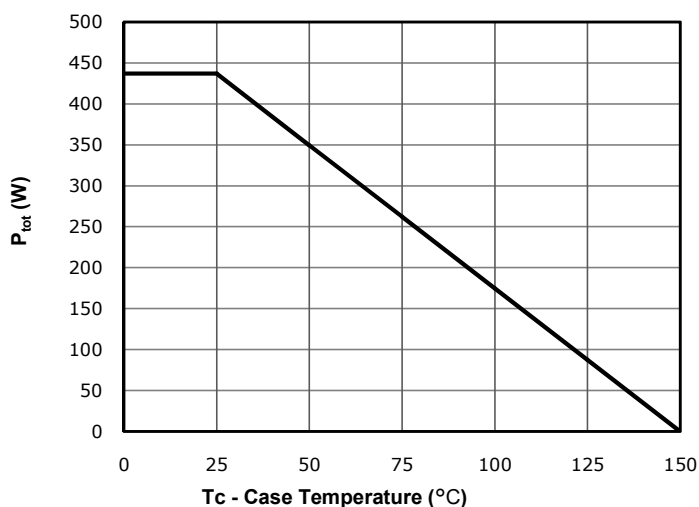


Fig 12: Drain Current Derating

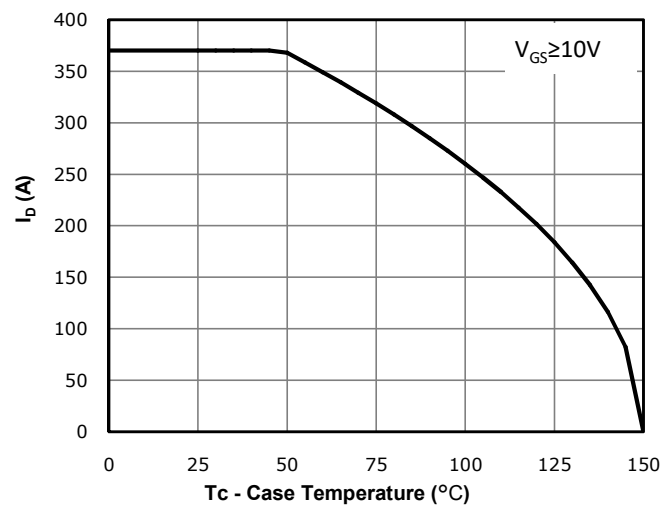


Fig 13: Safe Operating Area

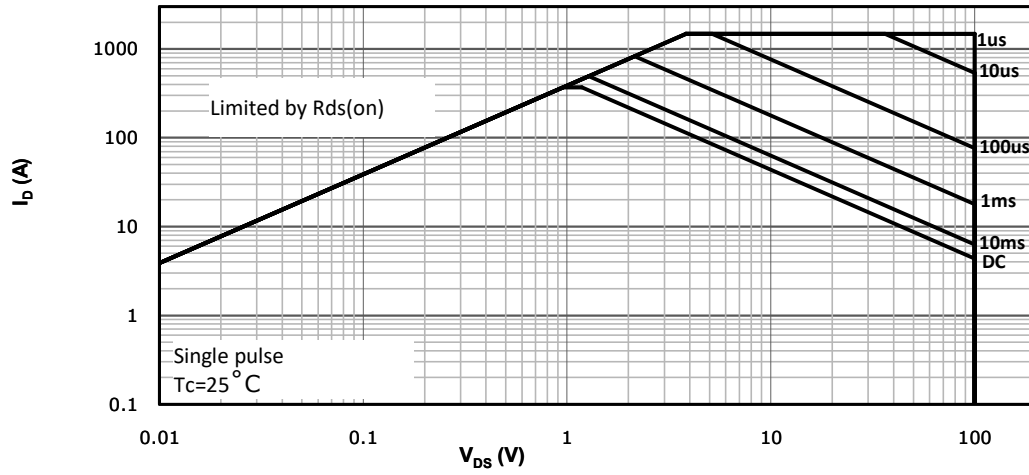
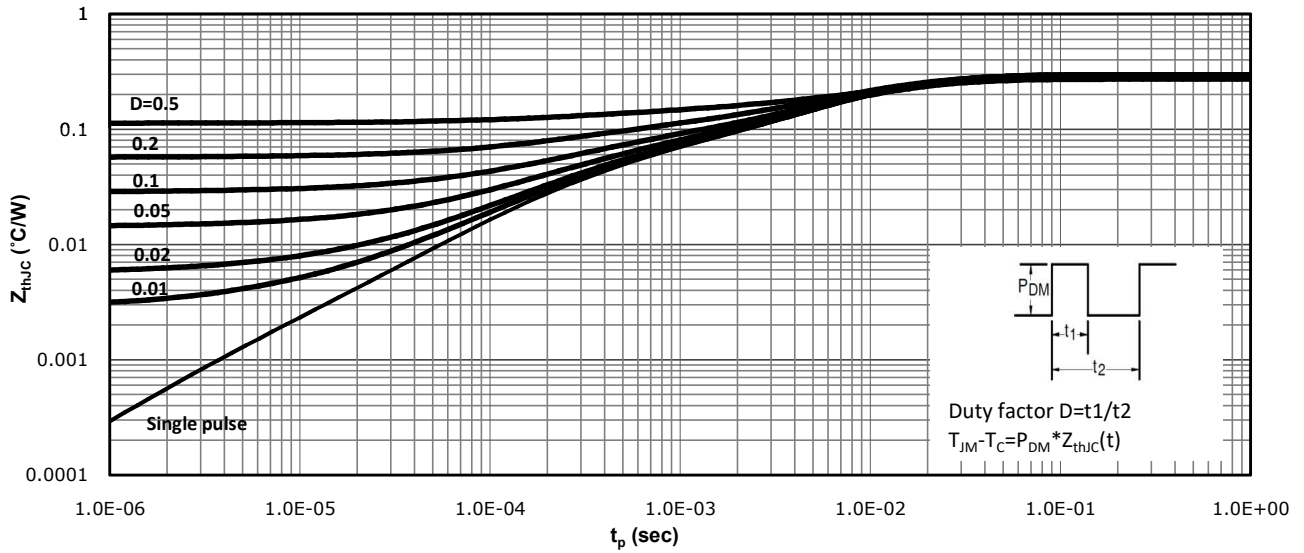
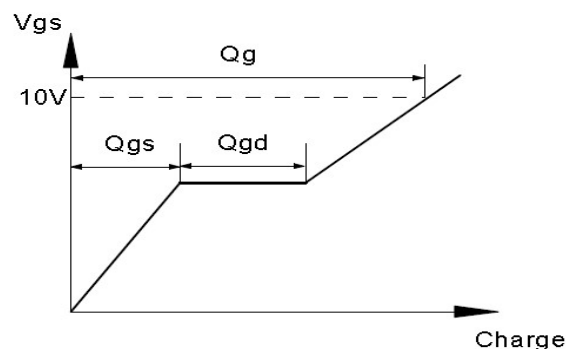
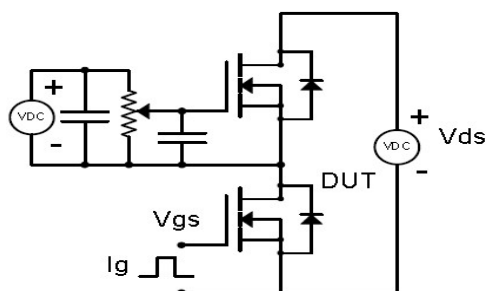


Fig 14: Max. Transient Thermal Impedance

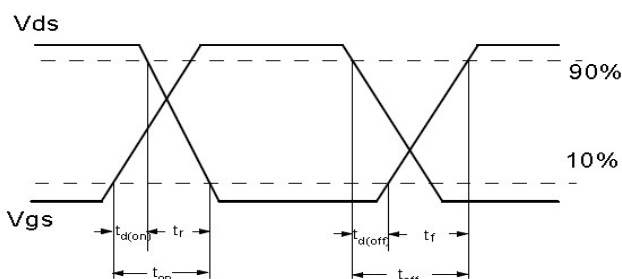
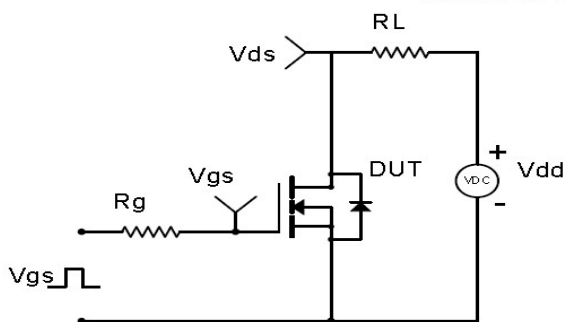


Test Circuit & Waveform

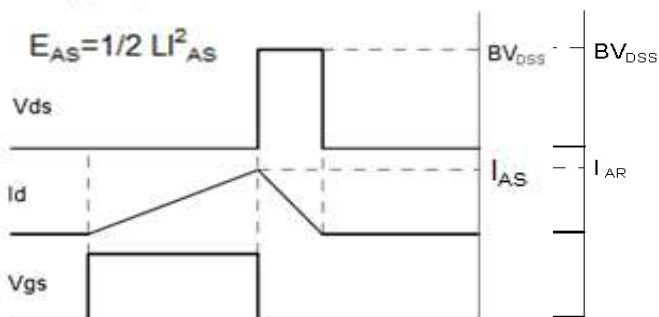
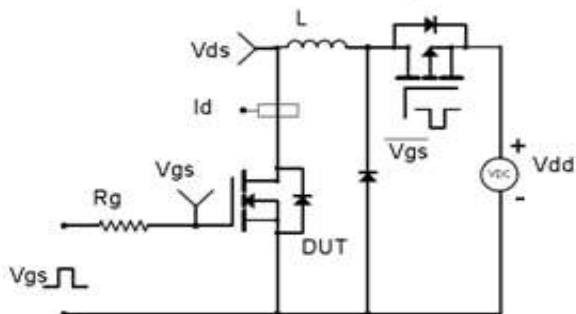
Gate Charge Test Circuit & Waveform



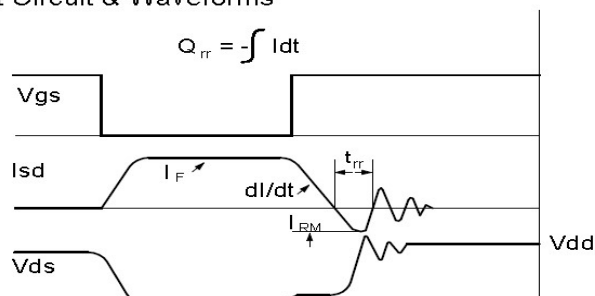
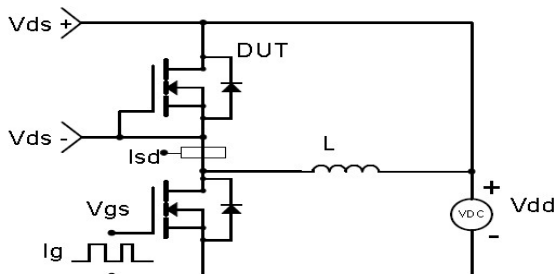
Resistive Switching Test Circuit & Waveforms



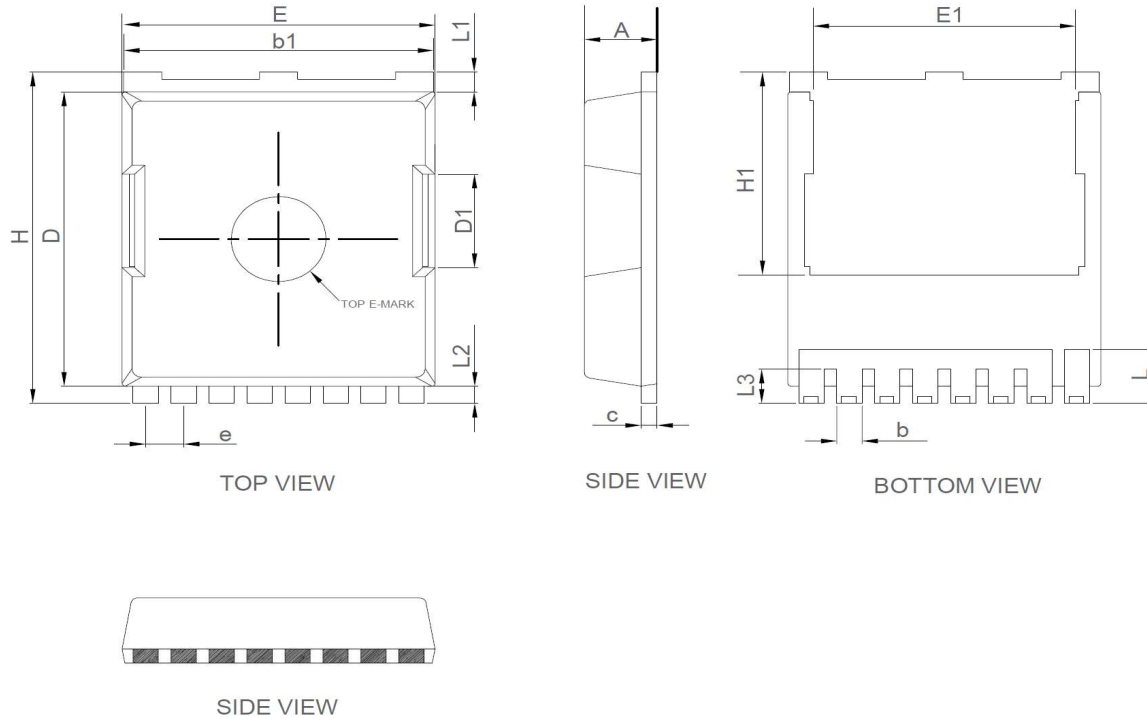
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline: TO11



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.15	2.45	0.085	0.096
b	0.60	0.90	0.024	0.035
b1	9.65	9.95	0.380	0.392
c	0.35	0.65	0.014	0.026
D	10.18	10.70	0.401	0.421
D1	3.15	3.45	0.124	0.136
E	9.70	10.10	0.382	0.398
E1	7.35	8.45	0.289	0.333
e	1.10	1.30	0.043	0.051
H	11.45	11.95	0.451	0.470
H1	6.55	7.50	0.258	0.295
L	1.35	2.10	0.053	0.083
L1	0.50	0.90	0.020	0.035
L2	0.40	0.80	0.016	0.031
L3	0.95	1.35	0.037	0.053

Marking**NOTE:**

NXBBAAAA-Y

N	—Wire Bond code
X	—Assembly location code
BB	—Fab code
AAAA	—Lot code
Y	—Bin code

Revision History

Revision	Date	Major changes
1.0	2024/7/9	Release of preliminary 1.0 version.

Disclaimer

CRM reserves the right to change any product or information in this Specification at any time without prior notice.

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